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Transition between strong and weak topological insulator in $ZrTe_5$ and $HfTe_5$

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$ZrTe_5$ and $HfTe_5$ have attracted increasingly attention recently since the theoretical prediction of being topological insulators (TIs). However, subsequent works show many contradictions about their topological nature. Three possible phases, i.e. strong TI, weak TI, and Dirac semi-metal, have been observed in different experiments until now. Essentially whether $ZrTe_5$ or $HfTe_5$ has a band gap or not is still a question. Here, we present detailed first-principles calculations on the electronic and topological properties of $ZrTe_5$ and $HfTe_5$ on variant volumes and clearly demonstrate the topological phase transition from a strong TI, going through an intermediate Dirac semi-metal phase, then to a weak TI when the crystal expands. Our work might give a unified explain about the divergent experimental results and propose the crucial clue to further experiments to elucidate the topological nature of these materials.

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I. INTRODUCTION

Topological insulator (TI) is a new class of material which is an insulator in its bulk, while having time reversal symmetry protected conducting states on the edge or surface. [1–3] A large number of realistic materials have been theoretically proposed and experimentally confirmed, such as Bi_2Se_3 and Bi_2Te_3. [4, 5] However, the layered transition-metal pentatelluride $ZrTe_5$ (and $HfTe_5$) is a particular example. $ZrTe_5$ and $HfTe_5$ have been studied more than 30 years ago due to the large thermoelectric power [6] and mysterious resistivity anomaly [7, 8]. Recently, Weng *et al.* predicted that mono-layer $ZrTe_5$ and $HfTe_5$ are good quantum spin Hall insulators with relatively large bulk band gap (about 0.1 eV) by first principles calculations. [9] And the three-dimensional bulk phase of $ZrTe_5$ and $HfTe_5$ are also predicted to be TIs, which are located at the vicinity of a transition between strong and weak TI, but without detailed description. [9]

Nevertheless, subsequent experiments show many contradictions about the topological nature of $ZrTe_5$ or $HfTe_5$. Several experimental works suggested that $ZrTe_5$ is a Dirac semi-metal without a finite band gap by different characterization methods, such as Shubnikov-de Haas oscillations, angle-resolved photoemission spectroscopy (ARPES), and infrared reflectivity measurements. [10–15] Of course there are also other experimental works holding opposite point of view. For example, in two recent scanning tunneling microscopy (STM) experiments, they unambiguously observed a large bulk band gap about 80 or 100 meV in $ZrTe_5$, [16, 17] implying that there is no surface state on the top surface and therefore it should be a weak TI. Another APRES work also favored a weak TI for $ZrTe_5$. [18] However, there are two other ARPES works which believed that $ZrTe_5$ is a strong TI. [19, 20] For instance, by using the comprehensive ARPES, STM, and first principles calculations, Manzoni *et al.* found a metallic DOS at Fermi energy, which arises from the two-dimensional surface state and thus indicates $ZrTe_5$ is a strong TI. [19]

The divergence of these experiments make $ZrTe_5$ ($HfTe_5$) being a very puzzling but interesting material, which needs more further experimental and theoretical studies. Therefore, in order to figure out the physical mechanism behind those contradictory experimental results, we revisited the band structures of $ZrTe_5$ and $HfTe_5$, and carefully studied their relationship with the volume expansion. We find a clear topological transition between a strong and weak TI in $ZrTe_5$ and $HfTe_5$, accompanied by a Dirac semi-metal phase between them. This work could shed more light on a unified explain about the different experimental results, and propose the crucial clue to further experiments to elucidate the topological nature of $ZrTe_5$ and $HfTe_5$.

II. COMPUTATIONAL METHODS

The geometric and electronic properties of $ZrTe_5$ and $HfTe_5$ are calculated by the density functional theory in the generalized gradient approximation implemented in the Vienna Ab-initio Simulation Package (VASP) code. [21, 22] The projected augmented wave method [23, 24] and the van der Waals (vdw) corrected optB86b-vdw functional [25, 26] are used. The plane-wave cutoff energy is 300 eV and the k-point mesh is $8 \times 8 \times 4$ in the calculations. And a denser k-point mesh is used in

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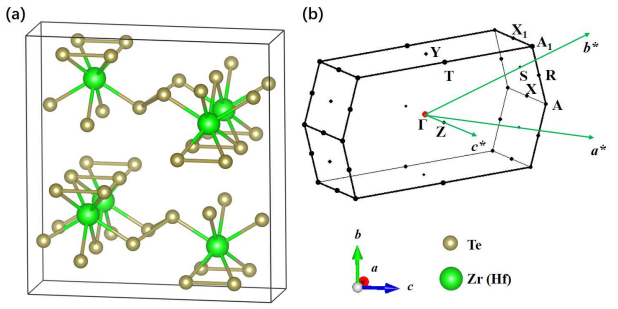

FIG. 1: (Color online) (**a**) Layered crystal stucture of $ZrTe_5$ ($HfTe_5$) in the orthorhombic conventional unit cell. Big green and small brown balls represent Zr (Hf) and Te atoms respectively. The layers stack along the b direction. (**b**) Brillouin zone and the high symmetry points of the primitive unit cell of $ZrTe_5$ ($HfTe_5$).

the density of state (DOS) calculation. Spin-orbit coupling (SOC) is included in the calculation except in the structural optimization.

The theoretical ground states of $ZrTe_5$ and $HfTe_5$ are obtained by fully optimization of the atom positions and lattice constants, until the maximal residual force is less than 0.01 eV/Å. Then we vary and fix the volumes of unit cell and still optimize the atom positions and lattice constants to study the possible topological transition in $ZrTe_5$ and $HfTe_5$.

III. RESULTS AND DISCUSSIONS

As shown in Fig. 1(a), $ZrTe_5$ and $HfTe_5$ share the same base-centered orthorhombic crystal structure, with Cmcm (No. 63) space group symmetry. Trigonal prismatic $ZrTe_3$ chains oriented along the a axis make up the $ZrTe_5$ natural cleavage plane. Each chain consists of one Zr atom and two different kinds of Te atoms. $ZrTe_3$ chains are connected by zigzag Te chains along the c axis, building a two dimensional structure of $ZrTe_5$ in the a-c plane. One crystal unit cell contains two $ZrTe_5$ planes piled along the b axis, the stack orientation of $ZrTe_5$. The Brillouin zone and its high symmetry k-points of $ZrTe_5$ ($HfTe_5$) are shown in Fig. 1(b), in which a^*, b^*, and c^* are the reciprocal lattice vectors.

Due to the weak vdw interaction in the layer $ZrTe_5$ ($HfTe_5$) [9], the vdw corrected correlation functional is necessary in order to obtain the good theoretical lattice constants. In Table I, we present the optimized lattice constants of $ZrTe_5$ and $HfTe_5$ based on the optB86b-vdw functional, as well as the experimental ones from reference [27]. We find that the theoretical and experimental lattice constants are well consistent with each other and the maximum difference between them is less than 1%. For comparison, we also optimized the structures of $ZrTe_5$ and $HfTe_5$ by using the standard Perdew-Burke-Ernzerhof (PBE) exchange correlation. [28] It is obvious that there is a large error (about 9 %) in the lattice b (in the stacking direction), which indicates that standard PBE failed to describe the structures of $ZrTe_5$ and$HfTe_5$, and the vdw correction is necessary.

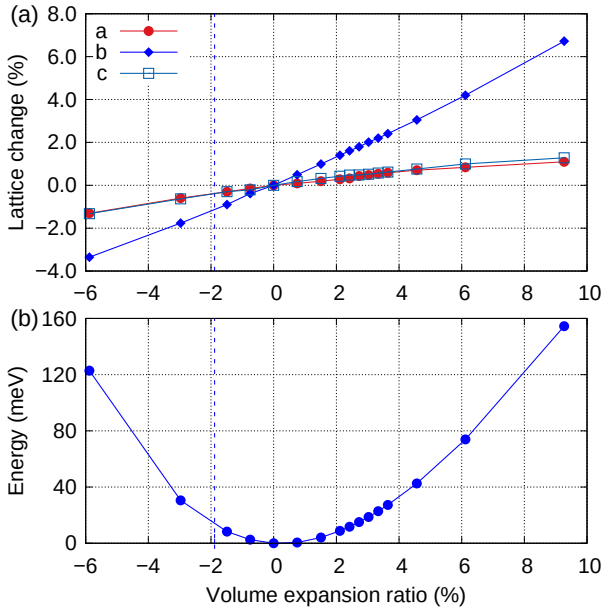

FIG. 2: (Color online) (**a**) Lattice constants a, b, and c under different unit cell volumes. (**b**) Relative total energy of a primitive unit cell of $ZrTe_5$ under different volumes. The blue vertical dotted lines represent the experimental volume at 10 K. [27]

In order to explore the possible topological phase transition in $ZrTe_5$ ($HfTe_5$), we then study their electronic properties under different volumes. Based on the above optimized structure, we change volume of the unit cell by hand and then optimize the atom positions and lattice constants under each variant volumes. This process can simulate the hydrostatic pressure experiments or the thermal expansion effect due to a finite temperatures. It is noted that we did not change the volume drastically, and the system is far away from the region of superconductivity phase under high pressure found in $ZrTe_5$ and $HfTe_5$. [29–31] In Fig. 2(a), we present the change of lattice constants a, b, and c under different volume expansion ratio, defined as $(V - V_0)/V_0 \times 100\%$, where V_0 is the unit cell volume at theoretical ground state listed in the Table I. It is found that all the lattice constants have similar linear dependence on the volume of the unit cell. But the in-plane lattice constants a and c changes much slower with the volume than that of the lattice constant b, which indicates the weak inter-layer binding energy along the b direction in $ZrTe_5$. The parabolic-like relationship between total energy of unit cell and volume is expected and given in Fig. 2 (b). The blue vertical dotted line represent the experimental volume at low temperature (10 K), which is nearly 1.9% smaller than our calculated value.

Then we have calculated the band structures and the

TABLE I: Calculated and experimental lattice constants and volumes of $ZrTe_5$ and $HfTe_5$ in conventional unit cell. Experimental data is from reference [27].

Material	Method	a (Å)	b (Å)	c (Å)	V (Å^3)
$ZrTe_5$	PBE	4.0490	15.772	13.845	884.17
	optB86b-vdw	4.0064	14.590	13.732	802.69
	exp. (293 K)	3.9875	14.530	13.724	795.15
	exp. (10 K)	3.9797	14.470	13.676	787.55
$HfTe_5$	PBE	4.0245	15.694	13.843	874.37
	optB86b-vdw	3.9799	14.564	13.743	796.58
	exp. (293 K)	3.9713	14.499	13.729	790.51
	exp. (10 K)	3.9640	14.443	13.684	783.44

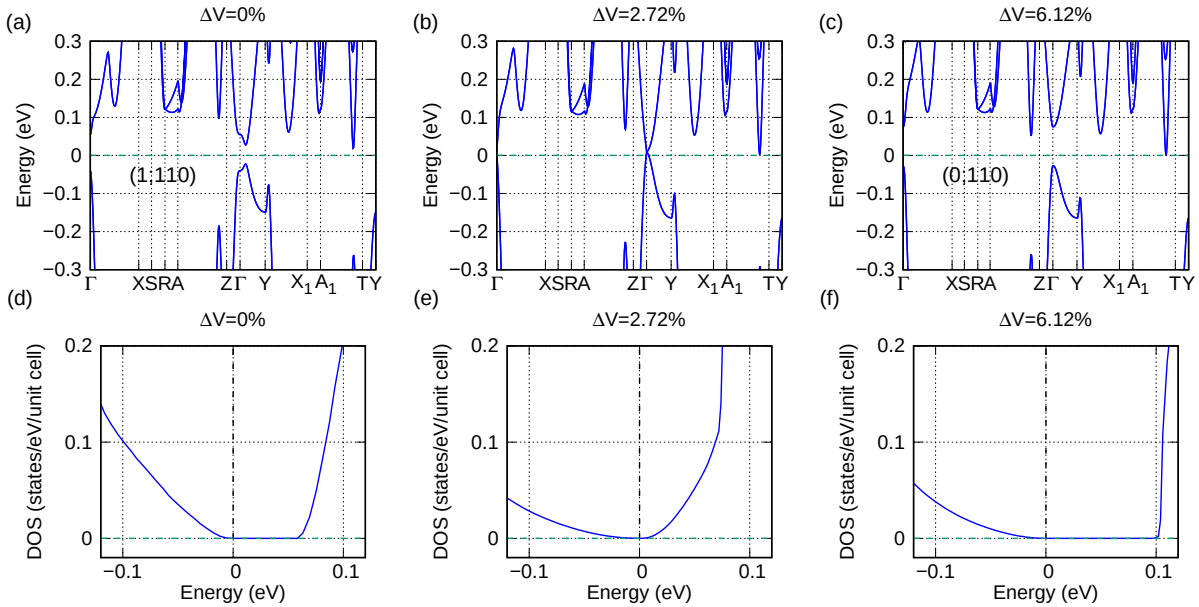

FIG. 3: (Color online) Band structures (**a-c**) and their corresponding DOSs (**d-f**) with SOC of $ZrTe_5$ under different volumes. The high-symmetry points are given in Fig. 1(b). Fermi energy is set as 0.

density of states (DOSs) with SOC under variant volumes, and three of them are shown in Fig. 3. The calculated band structure (Fig. 3 (a)) at the ground state volume ($\Delta V = 0$) is similar as previous theoretical computation [9], although we use a different high symmetry k-path. A clear direct band gap about 94.6 meV at Γ point is found in the band structure. Of course it is also found that the valence band maxima is between the Γ and Y point and conduction band minima is between the A_1 and T point. Therefore the indirect band gap is much smaller than the direct one at Γ point, which is about 41.7 meV in Fig. 3(a). The present of a clear band gap is confirmed in its corresponding DOS (Fig. 3 (d)). Our calculated band gap is comparable with the values observed in the previous experiments, [16, 17] which is 80 or 100 meV. Furthermore, it is found that the slop of DOS in the conduction band is much larger than that in the valence band, possibly because the conduction band has more valleys than the valence band. This characteristic is also found in the experiments. [16, 17]

When $ZrTe_5$ expands from its ground state , the band gap decreases gradually until the valence and conduction bands touch each other at a critical volume expansion ratio about 2.72%. Then, a Dirac point is formed at Γ point, which can be clearly seen in Fig. 3(b). This behavior is also confirmed in its corresponding V-shaped DOS near the Fermi energy, as shown in Fig. 3(e), which is the feature of Dirac point in band structure. As the crystal continues to expand, the band gap of $ZrTe_5$ opens again, and ultimately reaches a value of about 102.6 (direct) or 27.7 meV (indirect) under a volume expansion 6.12%. (see Figure 3 (c) and (f)). Therefore from Fig. 3, we can clearly see a transition from a semiconductor to a semi-metal and then to a semiconductor again in $ZrTe_5$ when it expands. In order to check whether such a transition is topological or not, we have calculated the Z_2 indices under each volume. [32] It is found that the Z_2 indices are all (1;110) when the volume expansion is

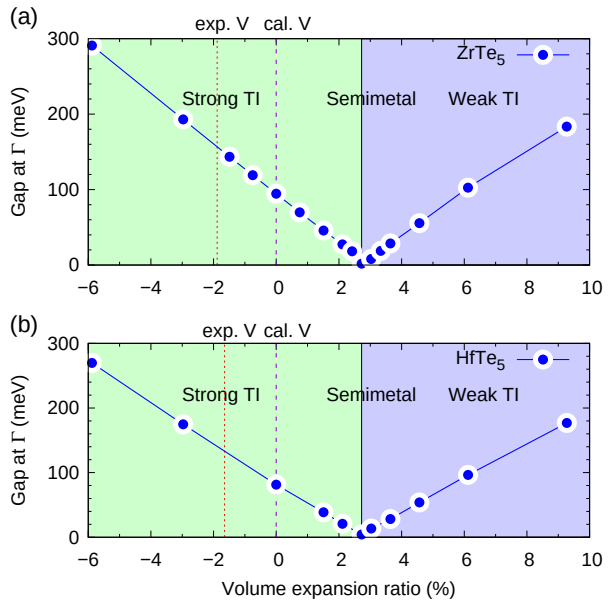

FIG. 4: (Color online) (**a**) Calculated absolute value of direct band gap at Γ point of $ZrTe_5$ under different volumes. The light green and blue region represent the phases of strong and weak TIs respectively. The boundary between the strong and weak TI is the semi-metal state. The red and blue dotted vertical lines represent the experimental volume at 10 K and calculated one at ground state respectively. (**b**) Same as (**a**) but for $HfTe_5$.

less than 2.72%, while it is (0;110) when the volumes expansion is larger than 2.72%. This definitively confirms that $ZrTe_5$ undergoes a topological phase transition from a strong TI, to a Dirac semi-metal, and finally turns to a weak TI when its unit cell expands from 0 to 6.12% in our calculation.

The detailed phase diagrams of such a topological phase transition of $ZrTe_5$ and $HfTe_5$ are given in Fig. 4, in which all the calculated absolute value of direct band gaps at Γ point under different volumes are plotted. In Fig. 4(a) we can find that the band gaps of $ZrTe_5$ decreases linearly as the volume increases from a negative volume expansion ratio about -6%, with a rate around -33 meV per 1% change of volume, where the negative value means a decrease of the band gap when the crystal expands. The band gap disappears at $\Delta V = 2.72\%$. Then it raises linearly with volume in a similar rate of 28 meV per 1% change of volume. Therefore $ZrTe_5$ undergoes a strong TI to weak TI topological phase transition due to volume expansion. Such a transition must need a zero-gap intermediate state, which is the semi-metal state found at about $\Delta V = 2.72\%$ in our calculation. Similar phase diagram is also proposed by a recent work, [20] in which they present the band gap at Γ point as a function of the inter-layer distance, but not the volume of the unit cell. In Fig. 4(b), we also show that $HfTe_5$ has the very similar topological phase transition, with almost the same transition critical volume expansion ratio at about 2.72%. The band gap of $HfTe_5$ also changes linearly as the volume increases with a rate about -31 and 26 meV per 1% change of volume in the strong and weak TI region respectively.

Such a band gap changing rate is quite significant especially in a small band gap semiconductor material. Therefore, we can conclude that the electronic properties of $ZrTe_5$ ($HfTe_5$) are indeed very sensitive to the change of the volume and they are indeed located very close to the boundary between the strong and weak TI. Although our optimized and the experimentally measured volume of $ZrTe_5$ ($HfTe_5$) both indicate that they should be within the strong TI region, we think it still has the possibility that in experiment $ZrTe_5$ ($HfTe_5$) can locate in a weak TI region due to different growth methods and characterization techniques in experiments. According to Fig. 4, it is even possible that $ZrTe_5$ ($HfTe_5$) can be in the Dirac semi-metal phase if it happens that its unit cell has a proper volume expansion ratio, which possibly been observed in many experiments. [10–15] Another more possible reason which can explain the semi-metal behavior found in these experiments is due to the defect and doping, which make the $ZrTe_5$ ($HfTe_5$) being a degenerate semiconductor. In a degenerate semiconductor, the Fermi energy is located within the conduction or valence band due to the doping effect, and the crystal will behave like a metal. But in this case, the energy gap still exist just below or above the Fermi energy and the Dirac point is not needed in the energy gap. In order to avoid the possible artificial effect induced by the cleavage in both STM and ARPES experiments, we suggest that nondestructive optical measurements for the existence of a direct band gap at Γ point, and its change under different temperatures, in the high quality and stoichiometric single crystals are probably useful to elucidate the topological nature in $ZrTe_5$ and $HfTe_5$.

Finally we show the importance of our calculated change rate of band gap. First we can roughly estimate the bulk thermal expansion coefficient from experimental lattice constants of $ZrTe_5$ (Table I) to be about 3.4×10^{-5} K^{-1}, which means that the volume will change about 1% when the temperature changes from 0 to 300 K, equivalently the band gap of $ZrTe_5$ at Γ point will change about -33 meV for strong TI phase or 28 meV for weak TI phase, according to our calculation. In a recent high-resolution ARPES work, [33] Zhang *et al.* found a clear and dramatic temperature dependent band gap in $ZrTe_5$, from which we then can estimate that change rate of observed band gap is about 26 or 37 meV from 0 to 300 K depending on the methods used in their experiment. These two values are both well consistent with our calcualted result. Moreover, the positive change rate found in the experiment [33] implies that the $ZrTe_5$ crystal used in their experiment is probably a weak TI according to our calculated phase diagram in Fig. 4.

IV. CONCLUSIONS

In conclusion, we have studied the band structures of $ZrTe_5$ and $HfTe_5$ at variant volume by first principles calculations. A clearly volume dependent strong and weak topological phase transition is found, accompanied by a zero-gap semi-metal phase at the boundary between the transition. The direct band gap of $ZrTe_5$ at Γ point changes linearly with the volume, which is -33 meV and 28 meV in a strong and weak TI phase respectively, if the volume of $ZrTe_5$ increases 1%, or equivalently if the temperature increases from 0 to 300 K. The results for $HfTe_5$ is very similar to thoese of $ZrTe_5$. Our calculated results indicate that the electronic properties and topological nature of $ZrTe_5$ and $HfTe_5$ are indeed very sensitive to the lattice constants of crystals, which is probably the reason for the divergent experimental results at present. We suggest that high quality and stoichiometric single crystal with accurate structure refinement at different temperatures would be helpful to resolve the divergent experimental results in $ZrTe_5$ and $HfTe_5$.

Acknowledgments

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